# DISCRETE POWER DIODES and THYRISTORS DATA BOOK



## **ST280S SERIES**

#### PHASE CONTROL THYRISTORS

#### **Stud Version**

#### **Features**

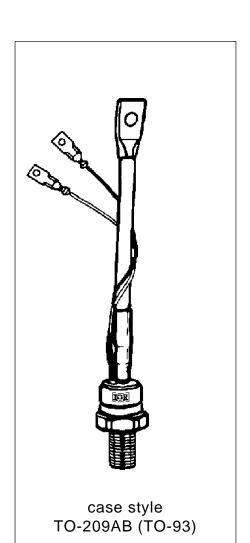
- Center amplifying gate
- Hermetic metal case with glass-metal seal insulator
- International standard case TO-209AB (TO-93)
- Threaded studs UNF 3/4 16UNF2A or ISO M16x1.5
- Compression Bonded Encapsulation for heavy duty operations such as severe thermal cycling

### **Typical Applications**

- DC motor controls
- Controlled DC power supplies
- AC controllers

## Major Ratings and Characteristics

Parameters		ST280S	Units	
I <sub>T(AV)</sub>		280	А	
	@ T <sub>C</sub>	85	°C	
I <sub>T(RMS)</sub>		440	А	
I <sub>TSM</sub>	@ 50Hz	7850	А	
	@ 60Hz	8220	А	
l <sup>2</sup> t @ 50Hz		308	KA <sup>2</sup> s	
	@ 60Hz	281	KA <sup>2</sup> s	
V <sub>DRM</sub> /V <sub>RRM</sub>		400 to 600	V	
t <sub>q</sub> typical		100	μs	
T <sub>J</sub>		- 40 to 125	°C	



280A

## **ELECTRICAL SPECIFICATIONS**

Voltage Ratings

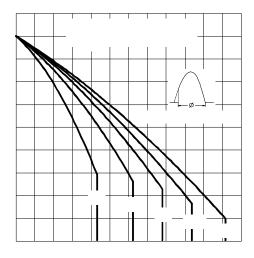
Type number	Voltage Code	V <sub>DRM</sub> /V <sub>RRM</sub> , max. repetitive peak and off-state voltage	V <sub>RSM</sub> , maximum non-repetitive peak voltage	$I_{DRM}/I_{RRM}$ max. @ $T_J = T_J$ max
		V	V	mA
ST280S	04	400	500	30
312003	06	600	700	30

### **On-state Conduction**

Parameter		ST280S	Units	Conditions		
I <sub>T(AV)</sub> Max. average on-state current		280	Α	180° conduction, half sine wave		
.()	@ Case temperature	85	°C			
I <sub>T(RMS)</sub>	Max. RMS on-state current	440	Α	DC @ 75°C case temperature		
I <sub>TSM</sub>	Max. peak, one-cycle	7850		t = 10ms	No voltage	
	non-repetitive surge current	8220		t = 8.3ms	reapplied	
		6600	A	t = 10ms	100% V <sub>RRM</sub>	
		6900		t = 8.3ms	reapplied	Sinusoidal half wave,
l²t	Maximum I2t for fusing	310		t = 10ms	No voltage	Initial $T_J = T_J$ max.
		220	KA <sup>2</sup> s	t = 8.3ms	reapplied	
		218	KA-S	t = 10ms	100% V <sub>RRM</sub>	
		200		t = 8.3ms	reapplied	
$I^2 \sqrt{t}$	Maximum $I^2 \sqrt{t}$ for fusing	3100	KA²√s	t = 0.1 to 10ms, no voltage reapplied		ge reapplied
V <sub>T(TO)1</sub>	Low level value of threshold voltage	0.84		V $(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}), T_{J} = V$ $(I > \pi \times I_{T(AV)}), T_{J} = T_{J} \text{ max.}$		$x I_{T(AV)}$ ), $T_J = T_J max$ .
V <sub>T(TO)2</sub>	High level value of threshold voltage	0.88	V			
r <sub>t1</sub>	Low level value of on-state slope resistance	0.50	mΩ	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}), T_J = T_{T(AV)}$		$x I_{T(AV)}$ ), $T_J = T_J max$ .
r <sub>t2</sub>	High level value of on-state slope resistance 0.47		11122	$(I > \pi \times I_{T(A)})$	$(V)$ , $T_J = T_J \text{ max}$	
$V_{TM}$	Max. on-state voltage	1.28	V	$I_{pk}$ = 880A, $T_J = T_J$ max, $t_p$ = 10ms sine pulse		p = 10ms sine pulse
I <sub>H</sub>	Maximum holding current	600		·		•
IL	Max. (typical) latching current	1000 (300)	mA	T <sub>J</sub> = 25°C, anode supply 12V resistive load		

## Switching

	Parameter	ST280S	Units	Conditions
di/dt	Max. non-repetitive rate of rise of turned-on current	1000	A/µs	Gate drive 20V, $20\Omega$ , $t_r \le 1 \mu s$ $T_J = T_J \text{ max, anode voltage} \le 80\% \text{ V}_{DRM}$
t <sub>d</sub>	Typical delay time	1.0		Gate current 1A, $di_g/dt = 1A/\mu s$ $V_d = 0.67\% V_{DRM}$ , $T_J = 25$ °C
tq	Typical turn-off time	100	μs	$I_{TM}$ = 300A, $T_J$ = $T_J$ max, di/dt = 20A/ $\mu$ s, $V_R$ = 50V dv/dt = 20V/ $\mu$ s, Gate 0V 100 $\Omega$ , $t_p$ = 500 $\mu$ s



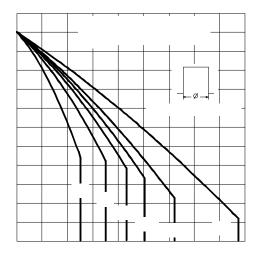


Fig. 1 - Current Ratings Characteristics

Fig. 2 - Current Ratings Characteristics

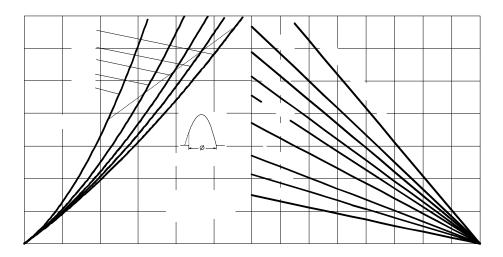


Fig. 3 - On-state Power Loss Characteristics

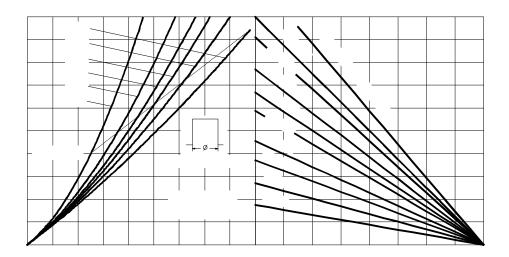
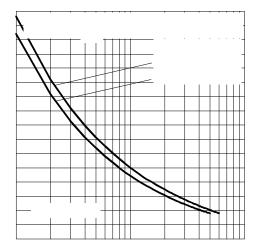


Fig. 4 - On-state Power Loss Characteristics



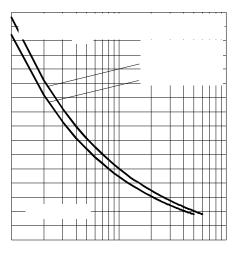


Fig. 5 - Maximum Non-Repetitive Surge Current

Fig. 6 - Maximum Non-Repetitive Surge Current

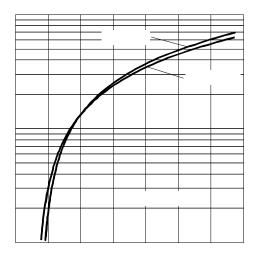


Fig. 7 - On-state Voltage Drop Characteristics

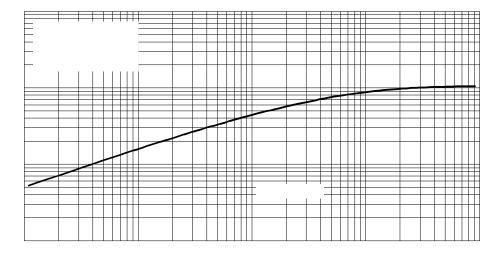


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristic

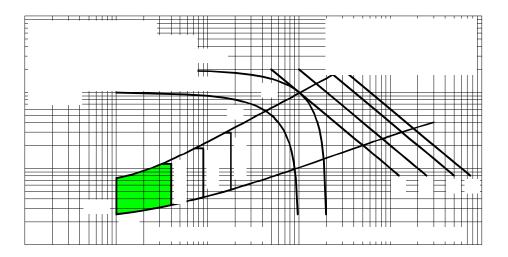


Fig. 9 - Gate Characteristics

## Blocking

	Parameter	ST280S	Units	Conditions
dv/dt	Maximum critical rate of rise of off-state voltage	500	V/µs	$T_J = T_J$ max linear to 80% rated $V_{DRM}$
I <sub>DRM</sub> I <sub>RRM</sub>	Max. peak reverse and off-state leakage current	30	mA	$T_J = T_J \text{ max, rated } V_{DRM}/V_{RRM} \text{ applied}$

## Triggering

	Parameter	ST280S		Units	Conditions	
P <sub>GM</sub>	Maximum peak gate power	10.0		W	$T_J = T_J \text{ max}, t_p$	≤ 5ms
P <sub>G(AV)</sub>	Maximum average gate power			VV	$T_J = T_J \text{ max, } f = 50 \text{Hz, } d\% = 50$	
I <sub>GM</sub>	Max. peak positive gate current	3.	0	Α	$T_J = T_J \text{ max, } t_p \le 5 \text{ms}$	
+V <sub>GM</sub>	Maximum peak positive	2	0			
	gate voltage	2	U	V	T - T may t	< 5mc
-V <sub>GM</sub>	Maximum peak negative	-	0	V	$T_J = T_J \text{ max, } t_p \le$	≥ 21112
	gate voltage	5.0				
		TYP.	MAX.			
I <sub>GT</sub>	DC gate current required	180	-		T <sub>J</sub> = - 40°C	
	to trigger	90	150	mA	$T_J = 25^{\circ}C$	Max. required gate trigger/ cur-
		40	-		T <sub>J</sub> = 125°C	rent/voltage are the lowest value which will trigger all units 12V
V <sub>GT</sub>	DC gate voltage required	2.9	-		T <sub>J</sub> = - 40°C	anode-to-cathode applied
	to trigger	1.8	3.0	V	$T_J = 25^{\circ}C$	
		1.2	1		T <sub>J</sub> = 125°C	
I <sub>GD</sub>	DC gate current not to trigger	0.25		mA		Max. gate current/ voltage not to
V <sub>GD</sub>	DC gate voltage not to trigger			V	$T_J = T_J \text{ max}$	trigger is the max. value which will not trigger any unit with rated V <sub>DRM</sub> anode-to-cathode applied

## Thermal and Mechanical Specification

	Parameter	ST280S	Units	Conditions
T <sub>J</sub>	Max. operating temperature range	-40 to 125	0.0	
T <sub>stg</sub>	Max. storage temperature range	-40 to 150	°C	
R <sub>thJC</sub>	Max. thermal resistance, junction to case	0.105	K/W	DC operation
R <sub>thCS</sub>	Max. thermal resistance, case to heatsink	0.04	K/W	Mounting surface, smooth, flat and greased
Т	Mounting torque, ± 10%	31		No. 1. before to the conde
		(275)	Nm	Non lubricated threads
		24.5	(lbf-in)	I what and the sounds
		(210)		Lubricated threads
wt	Approximate weight	280	g	
	Case style	TO - 209AB (TO	-93)	See Outline Table

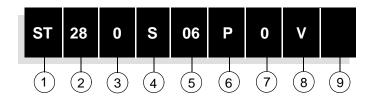
## $\Delta R_{\rm thJC}$ Conduction

(The following table shows the increment of thermal resistence  $R_{thJC}$  when devices operate at different conduction angles than DC)

_					
	Conduction angle	Sinusoidal conduction	Rectangular conduction	Units	Conditions
Ī	180°	0.016	0.012		$T_J = T_J \text{ max.}$
ſ	120°	0.019	0.020		
I	90°	0.025	0.027	K/W	
I	60°	0.036	0.037		
	30°	0.060	0.060		

#### Ordering Information Table

#### **Device Code**



- 1 Thyristor
- Essential part number
- 3 0 = Converter grade
- S = Compression bonding Stud
- 5 Voltage code: Code x 100 = V<sub>RRM</sub> (See Voltage Rating Table)
- 6 P = Stud base 16UNF threads
  - M = Stud base metric threads (M16 x 1.5)
- 7 0 = Eyelet terminals (Gate and Auxiliary Cathode Leads)
  - 1 = Fast on terminals (Gate and Auxiliary Cathode Leads)
  - 2 = Flag terminals (For Cathode and Gate Terminals)
- V = Glass-metal seal
- 9 Critical dv/dt: None = 500V/µsec (Standard selection)

L = 1000V/µsec (Special selection)

#### **Outline Table**

